AMENDMENTS TO THE CLAIMS

Please amend claim 6 as noted in the following listing of all pending claims.

1-5. (Cancelled.)

6. (Currently Amended) A semiconductor laser comprising:

a light emission function layer stack including a cladding layer and an active layer formed on ~~one plane~~ a first surface of a translucent substrate;

two electrodes having different polarities, which are provided on said light emission function layer stack side; and

a light leakage preventive film formed on ~~the other plane~~ a second surface of said translucent substrate that is opposite said first surface, wherein the light emission function layer stack provides a resonator direction parallel to the first and second surfaces and said light leakage prevention film prevents light leakage in a direction perpendicular to the resonator direction.

7. (Original) A semiconductor laser according to claim 6, wherein said light leakage preventive film comprises a light absorbing film.

8. (Original) A semiconductor laser according to claim 6, wherein said light leakage preventive film comprises a light reflecting film.

9. (Original) A semiconductor laser according to claim 6, wherein said light leakage preventive film comprises a dielectric film.

10. (Original) A semiconductor laser according to claim 6, wherein said light leakage preventive film comprises a metal film.

11. (Original) A semiconductor laser according to claim 6, wherein a thickness of said light leakage preventive film is set to a value of $\lambda/4n$ where λ is a wavelength of light emitted from said light emission function layer stack and n is a refractive index of said light leakage preventive film.

12. (Original) A semiconductor laser according to claim 6, wherein said light leakage preventive film comprises a multi-layer film of dielectrics, and a thickness of each layer of said multi-layer film of dielectrics is set to a value of $\lambda/4n$ where λ is a wavelength of light emitted from said light emission function layer stack and n is a refractive index of said light leakage preventive film.

13. (Original) A semiconductor laser according to claim 6, wherein each layer of said light emission function layer stack is made from a GaN base semiconductor.

14. (Original) A semiconductor laser according to claim 6, wherein said translucent substrate is made from sapphire.

15. (Original) A semiconductor laser according to claim 6, wherein said translucent substrate is made from GaN.

16-22 (Cancelled).